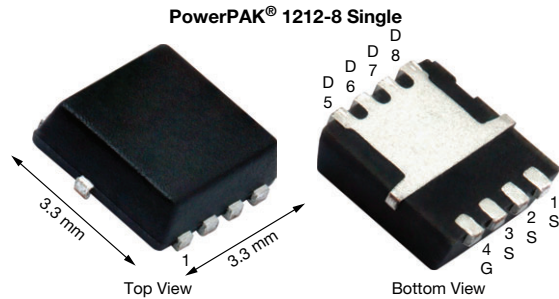




**THE DATASHEET OF
SISC06DN-T1-GE3**



N-Channel 30 V (D-S) MOSFET



FEATURES

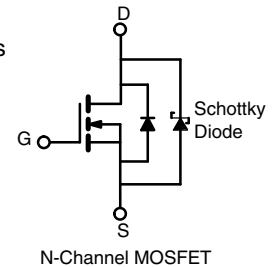
- TrenchFET® Gen IV power MOSFET
- SkyFET® with monolithic Schottky diode
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Personal computers and servers
- Synchronous buck
- Synchronous rectification
- DC/DC conversion



PRODUCT SUMMARY	
V _{DS} (V)	30
R _{DS(on)} max. (Ω) at V _{GS} = 10 V	0.0027
R _{DS(on)} max. (Ω) at V _{GS} = 4.5 V	0.0040
Q _g typ. (nC)	17.5
I _D (A)	40 ^g
Configuration	Single

ORDERING INFORMATION	
Package	PowerPAK 1212-8
Lead (Pb)-free and halogen-free	SiSC06DN-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	30	V
Gate-source voltage		V _{GS}	+20, -16	
Continuous drain current (T _J = 150 °C)	T _C = 25 °C	I _D	40 ^g	A
	T _C = 70 °C		40 ^g	
	T _A = 25 °C		27.6 ^{a, b}	
	T _A = 70 °C		25.2 ^{a, b}	
Pulsed drain current (t = 100 μs)		I _{DM}	100	
Continuous source-drain diode current	T _C = 25 °C	I _S	40 ^g	
	T _A = 25 °C		3.3 ^{a, b}	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	15	mJ
Single pulse avalanche energy		E _{AS}	11.25	
Maximum power dissipation	T _C = 25 °C	P _D	46.3	W
	T _C = 70 °C		29.6	
	T _A = 25 °C		3.7 ^{a, b}	
	T _A = 70 °C		3.1 ^{a, b}	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C
Soldering recommendations (peak temperature) ^{c, d}			260	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^{a, e}	t ≤ 10 s	R _{thJA}	25	33	°C/W
Maximum junction-to-case (drain)	Steady state	R _{thJC}	2.1	2.7	

Notes

- Surface mounted on 1" x 1" FR4 board
- t = 10 s
- See solder profile (www.vishay.com/doc?73257). The PowerPAK 1212-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 81 °C/W
- Based on T_C = 25 °C
- Package limited



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30	-	-	V	
Drain-source breakdown voltage (transient) ^c	V _{DSt}	V _{GS} = 0 V, I _{D(aval)} = 15 A, t _{transient} ≤ 50 ns	36	-	-		
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	1	-	2.1		
Gate-source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = +20 V, -16 V	-	-	± 100	nA	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	-	0.02	0.20	mA	
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C	-	0.13	1		
On-state drain current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	30	-	-	A	
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 15 A	-	0.0022	0.0027	Ω	
		V _{GS} = 4.5 V, I _D = 10 A	-	0.0032	0.0040		
Forward transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 15 A	-	120	-	S	
Dynamic^b							
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz	-	2455	-	pF	
Output capacitance	C _{oss}		-	350	-		
Reverse transfer capacitance	C _{rss}		-	60	-		
C _{rss} /C _{iss} ratio			-	0.025	0.050		
Total gate charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A	-	38.5	58	nC	
		V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 10 A	-	17.5	27		
Gate-source charge	Q _{gs}		-	6.3	-		
Gate-drain charge	Q _{gd}		-	2.8	-		
Output charge	Q _{oss}	V _{DS} = 15 V, V _{GS} = 0 V	-	29	-		
Gate resistance	R _g	f = 1 MHz	0.4	1.15	2	Ω	
Turn-on delay time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 4.5 V, R _g = 1 Ω	-	12	24	ns	
Rise time	t _r		-	14	28		
Turn-off delay time	t _{d(off)}		-	23	46		
Fall time	t _f		-	8	16		
Turn-on delay time	t _{d(on)}	V _{DD} = 15 V, R _L = 1.5 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω	-	29	58		
			Rise time	t _r	-		50
Turn-off delay time	t _{d(off)}			-	20		40
	Fall time			t _f	-		9
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I _S	T _C = 25 °C	-	-	40	A	
Pulse diode forward current	I _{SM}		-	-	100		
Body diode voltage	V _{SD}	I _S = 5 A, V _{GS} = 0 V	-	0.47	0.7	V	
Body diode reverse recovery time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs, T _J = 25 °C	-	31	62	ns	
Body diode reverse recovery charge	Q _{rr}		-	19	38	nC	
Reverse recovery fall time	t _a		-	16	-	ns	
Reverse recovery rise time	t _b		-	15	-		

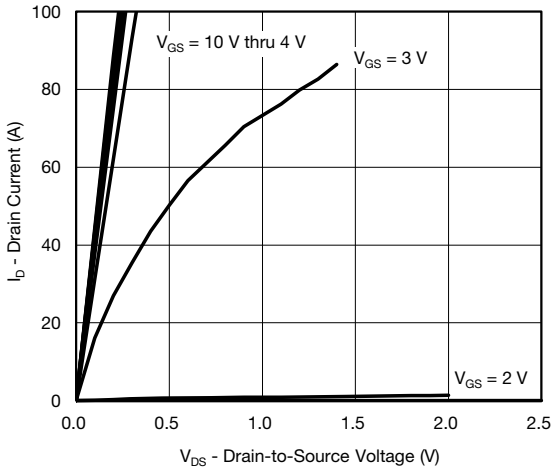
Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %
- Guaranteed by design, not subject to production testing
- T_{CASE} = 25 °C; Expected voltage stress during 100 % UIS test. Production data log is not available

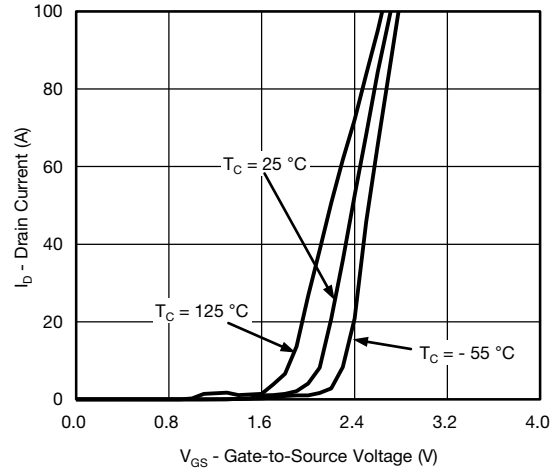
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



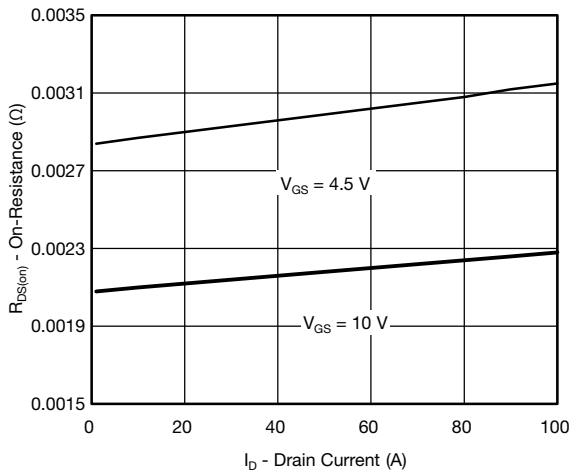
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



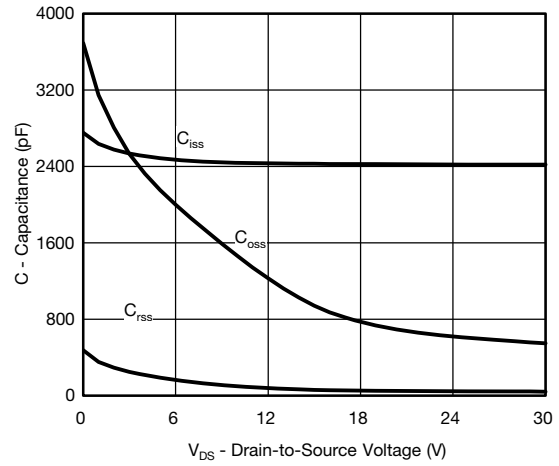
Output Characteristics



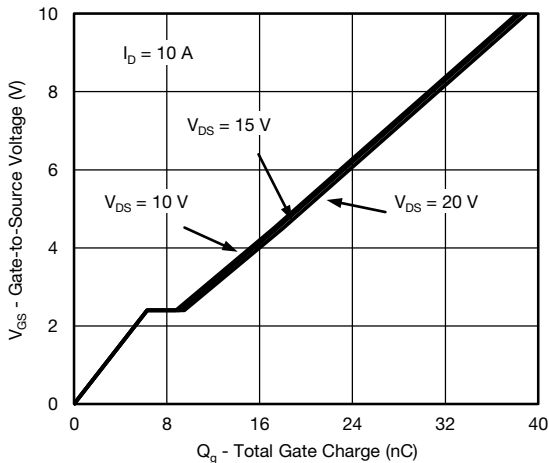
Transfer Characteristics



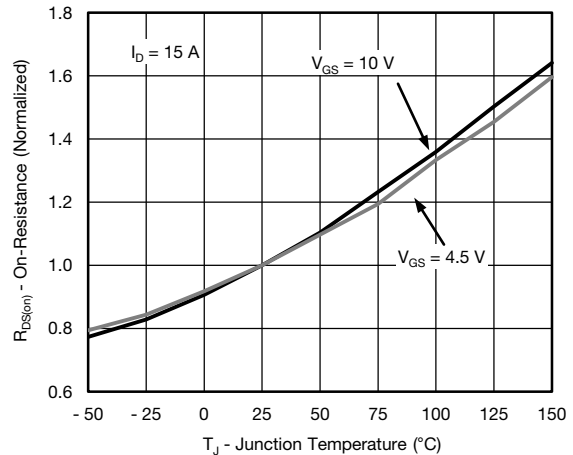
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



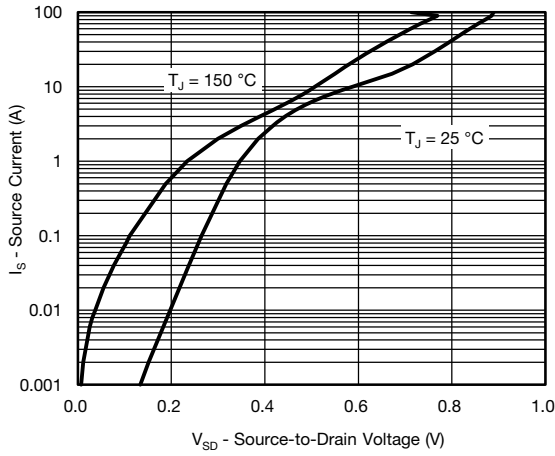
Gate Charge



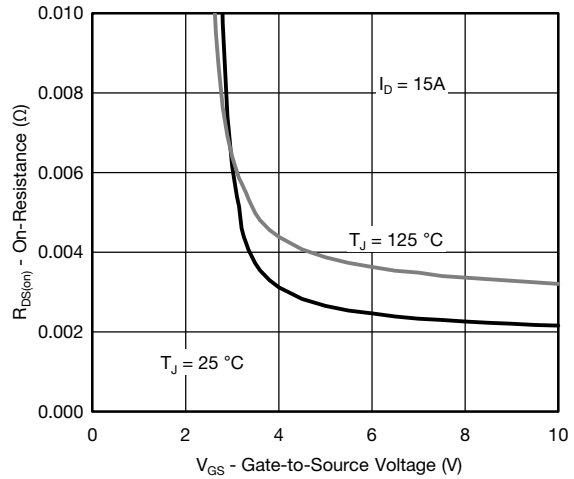
On-Resistance vs. Junction Temperature



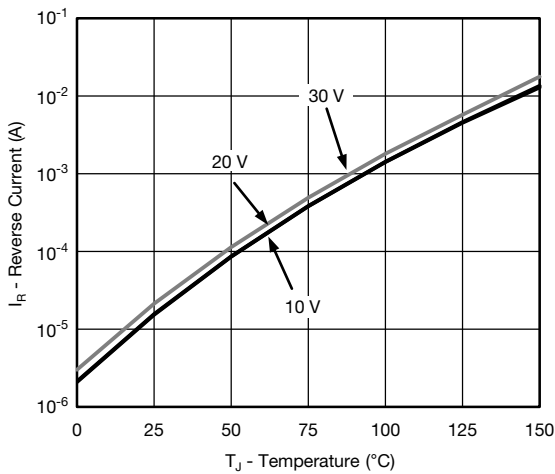
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



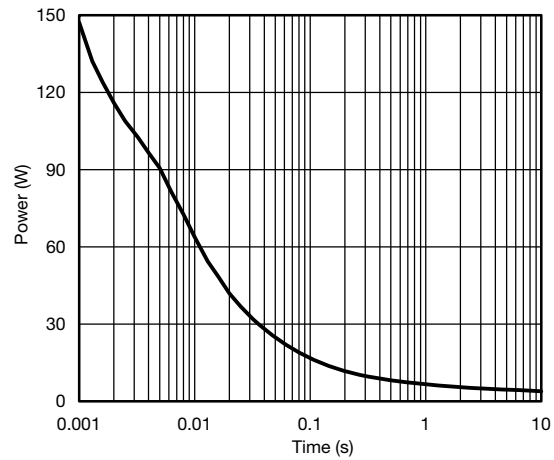
Source-Drain Diode Forward Voltage



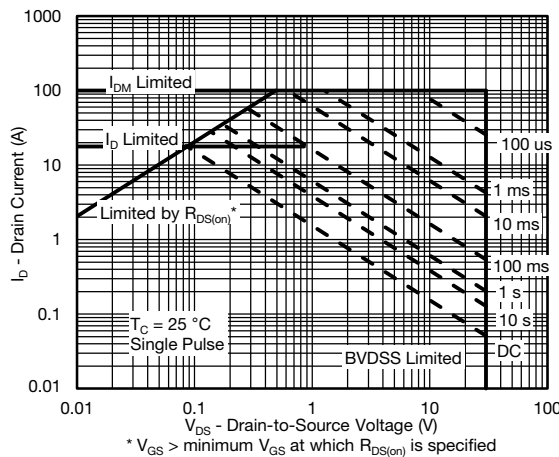
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



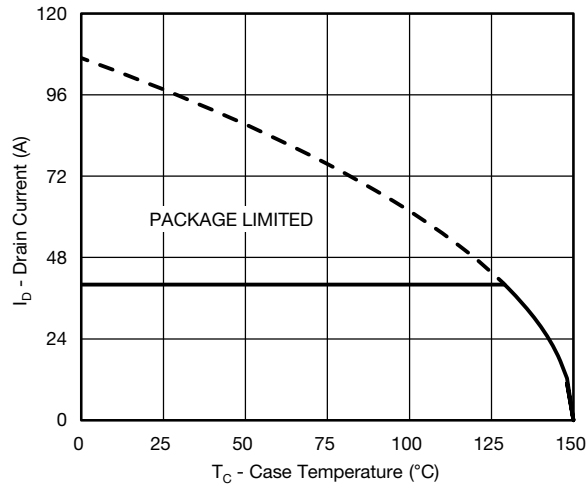
Single Pulse Power, Junction-to-Ambient



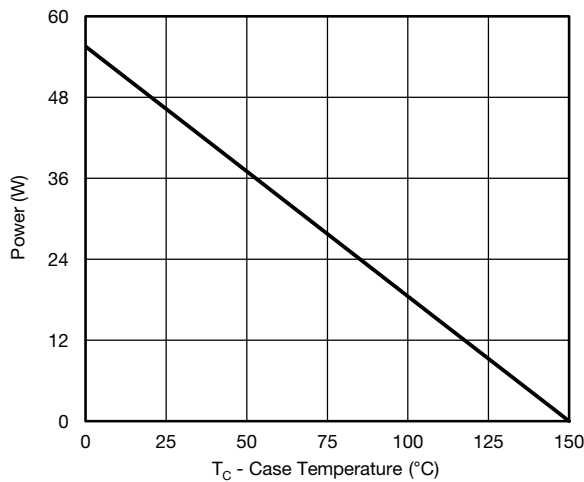
Safe Operating Area, Junction-to-Ambient



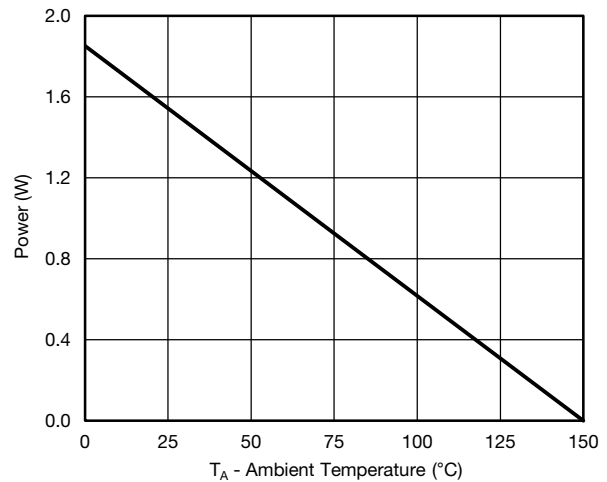
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating ^a



Power, Junction-to-Case



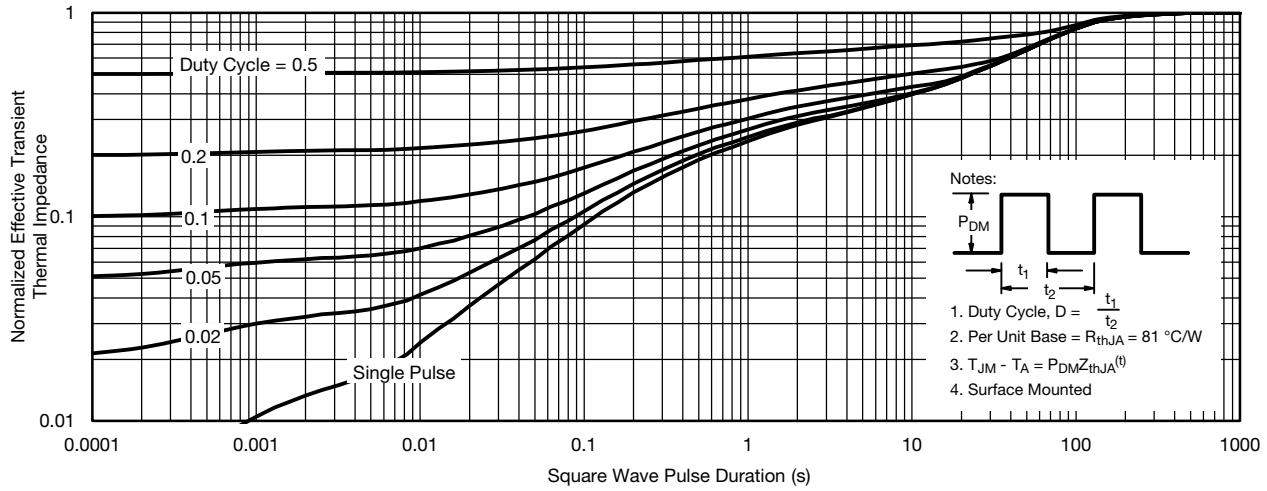
Power, Junction-to-Ambient

Note

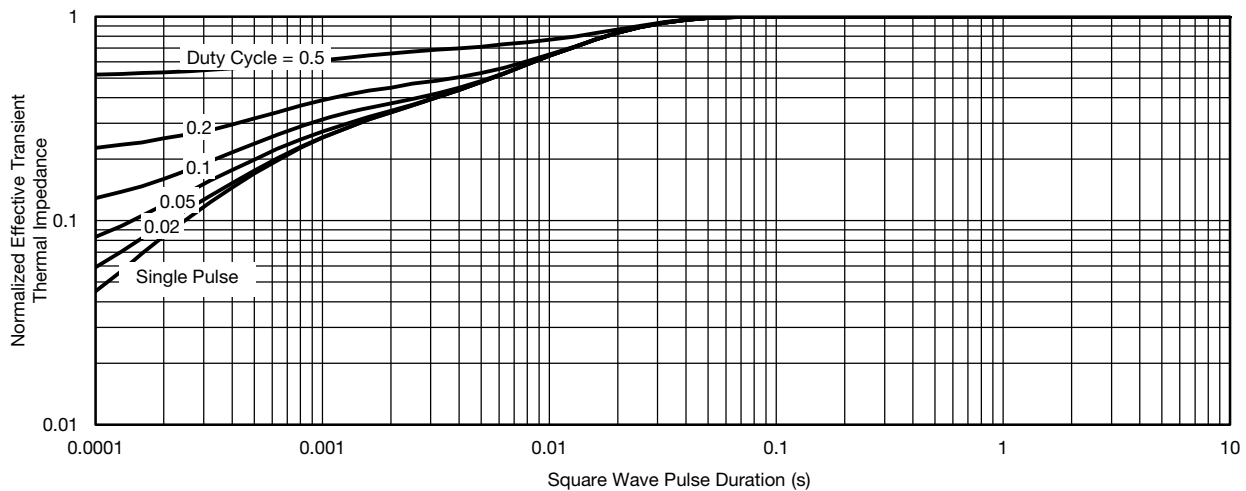
a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK® 1212-8, (Single / Dual)



- Notes**
 1. Inch will govern
 [2] Dimensions exclusive of mold gate burrs
 3. Dimensions exclusive of mold flash and cutting burrs

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.97	1.04	1.12	0.038	0.041	0.044
A1	0.00	-	0.05	0.000	-	0.002
b	0.23	0.30	0.41	0.009	0.012	0.016
c	0.23	0.28	0.33	0.009	0.011	0.013
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
D3	0.48	-	0.89	0.019	-	0.035
D4	0.47 typ.			0.0185 typ		
D5	2.3 typ.			0.090 typ		
E	3.20	3.30	3.40	0.126	0.130	0.134
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	1.75	1.85	1.98	0.069	0.073	0.078
E4	0.034 typ.			0.013 typ.		
e	0.65 BSC			0.026 BSC		
K	0.86 typ.			0.034 typ.		
K1	0.35	-	-	0.014	-	-
H	0.30	0.41	0.51	0.012	0.016	0.020
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
M	0.125 typ.			0.005 typ.		

ECN: S16-2667-Rev. M, 09-Jan-17
 DWG: 5882

RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads
Dimensions in Inches/(mm)

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